



**COPY**

MICRON.009DV1

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

10/B  
8/6/99  
JProchn

Applicant	:	Schuegraf et al.	)	Group Art Unit 2811
Appl. No.	:	08/932,228	)	
Filed	:	September 17, 1997	)	
For	:	SHALLOW TRENCH ISOLATION USING LOW DIELECTRIC CONSTANT INSULATOR	)	
Examiner	:	Hung K. Vu	)	
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**AMENDMENT AND RESPONSE TO OFFICE ACTION**

**RECEIVED**

APR 03 1999

Assistant Commissioner for Patents  
Washington, D.C. 20231

TECHNOLOGY CENTER 2800

Dear Sir:

In response to the office action, mailed August 12, 1998, please amend the above-referenced application as indicated below.

**IN THE CLAIMS:**

~~11. (Amended) An isolation structure in a semiconductor substrate comprising:~~  
~~a recessed portion formed therein in the semiconductor substrate; and~~  
~~a dielectric material comprising a halide-doped silicon oxide filling the recessed portion,~~  
~~said dielectric material having a dielectric constant lower than the dielectric constant of silicon~~  
~~dioxide.~~